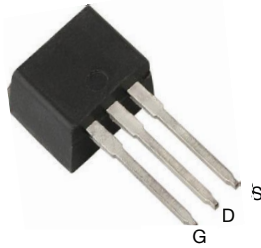


CMI120N04A-VB Datasheet

N-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY

| V_{DS} (V) | $R_{DS(on)}$ (Ω) | I_D (A) ^{a, c} | Q_g (Typ.) |
|--------------|----------------------------|---------------------------|--------------|
| 40 | 0.0017 at $V_{GS} = 10$ V | 150 | 120 nC |
| | 0.0025 at $V_{GS} = 4.5$ V | 135 | |

TO-262

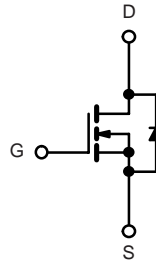
Top View

FEATURES

- Trench Power MOSFET
- 100 % R_g and UIS Tested

APPLICATIONS

- Synchronous Rectification
- Power Supplies



N-Channel MOSFET


RoHS
 COMPLIANT
ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

| Parameter | | Symbol | Limit | Unit |
|--|--------------------------|----------------|---------------------|------------------|
| Drain-Source Voltage | | V_{DS} | 40 | V |
| Gate-Source Voltage | | V_{GS} | ± 25 | |
| Continuous Drain Current ($T_J = 175^\circ\text{C}$) | $T_C = 25^\circ\text{C}$ | I_D | 150 ^{a, c} | A |
| | $T_C = 70^\circ\text{C}$ | | 120 ^c | |
| | $T_A = 25^\circ\text{C}$ | | 29 ^b | |
| | $T_A = 70^\circ\text{C}$ | | 23 ^b | |
| Pulsed Drain Current | | I_{DM} | 380 | |
| Avalanche Current Pulse | | I_{AS} | 80 | |
| Single Pulse Avalanche Energy | | E_{AS} | 320 | mJ |
| Continuous Source-Drain Diode Current | $T_C = 25^\circ\text{C}$ | I_S | 110 ^{a, c} | A |
| | $T_A = 25^\circ\text{C}$ | | 2.6 ^b | |
| Maximum Power Dissipation | $T_C = 25^\circ\text{C}$ | P_D | 312 ^a | W |
| | $T_C = 70^\circ\text{C}$ | | 200 | |
| | $T_A = 25^\circ\text{C}$ | | 3.13 ^b | |
| | $T_A = 70^\circ\text{C}$ | | 2.0 ^b | |
| Operating Junction and Storage Temperature Range | | T_J, T_{stg} | - 55 to 150 | $^\circ\text{C}$ |

THERMAL RESISTANCE RATINGS

| Parameter | | Symbol | Typical | Maximum | Unit |
|--|--------------|------------|---------|---------|--------------------|
| Maximum Junction-to-Ambient ^b | Steady State | R_{thJA} | 32 | 40 | $^\circ\text{C/W}$ |
| | Steady State | R_{thJC} | 0.33 | 0.4 | |

Notes:

a. Based on $T_C = 25^\circ\text{C}$.

b. Surface Mounted on 1" x 1" FR4 board.

c. Calculated based on maximum junction temperature. Package limitation current is 110 A.

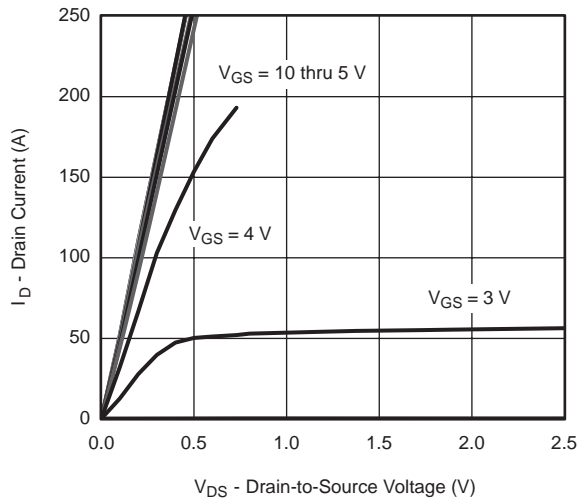
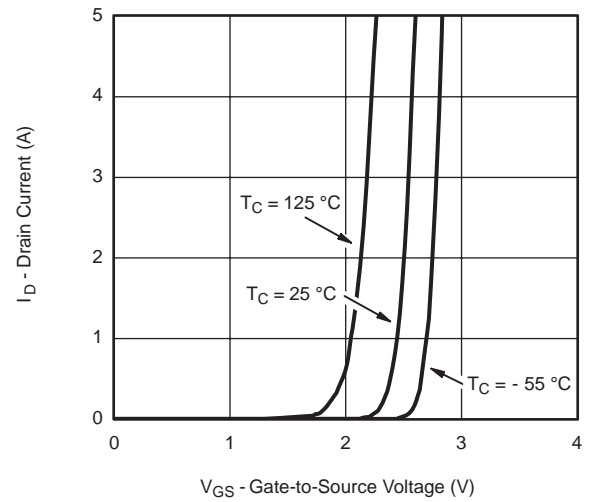
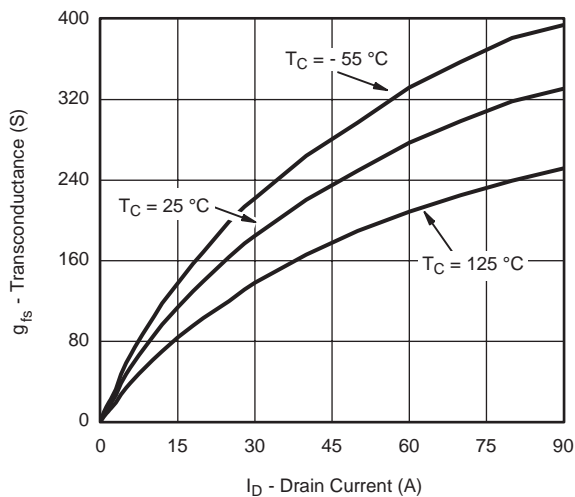
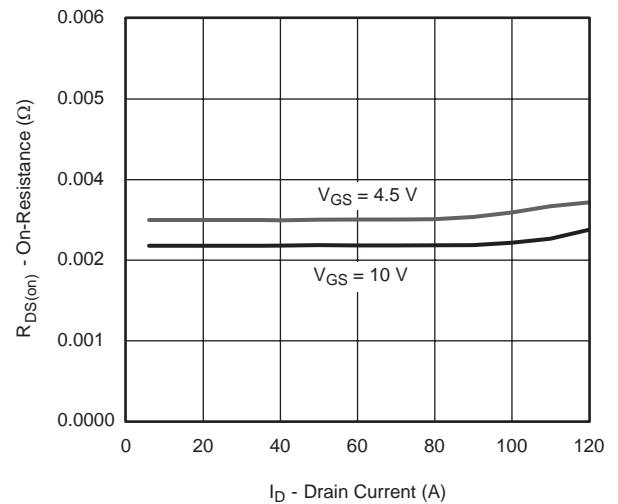
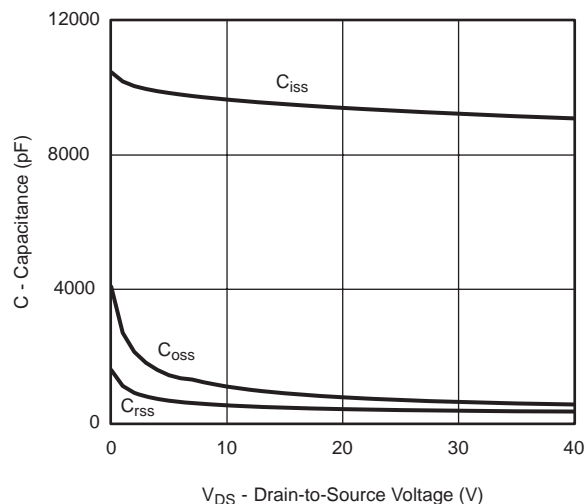
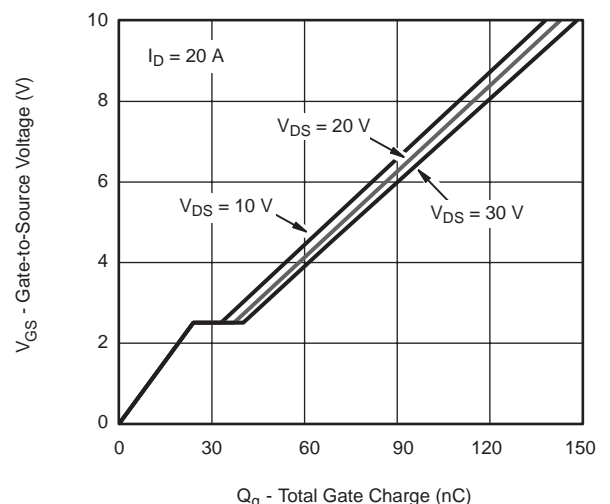
| SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted | | | | | | |
|--|-------------------------|---|------|--------|-----------|------------------------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | 45 | | | V |
| V_{DS} Temperature Coefficient | $\Delta V_{DS}/T_J$ | $I_D = 250\text{ }\mu\text{A}$ | | 41 | | mV/ $^{\circ}\text{C}$ |
| $V_{GS(th)}$ Temperature Coefficient | $\Delta V_{GS(th)}/T_J$ | | | - 8 | | |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | 1.2 | | 2.5 | V |
| Gate-Source Leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}$ | | | 1 | μA |
| | | $V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^{\circ}\text{C}$ | | | 10 | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$ | 120 | | | A |
| Drain-Source On-State Resistance ^a | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}, I_D = 30\text{ A}$ | | 0.0017 | | Ω |
| | | $V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$ | | 0.0025 | | |
| Forward Transconductance ^a | g_{fs} | $V_{DS} = 15\text{ V}, I_D = 30\text{ A}$ | | 180 | | S |
| Dynamic ^b | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | | 9000 | | pF |
| Output Capacitance | C_{oss} | | | 650 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 450 | | |
| Total Gate Charge | Q_g | $V_{DS} = 20\text{ V}, V_{GS} = 10\text{ V}, I_D = 20\text{ A}$ | | 120 | 180 | nC |
| Gate-Source Charge | Q_{gs} | | | 30 | | |
| Gate-Drain Charge | Q_{gd} | | | 16 | | |
| Gate Resistance | R_g | $f = 1\text{ MHz}$ | | 0.85 | 1.3 | Ω |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = 20\text{ V}, R_L = 1.0\text{ }\Omega$ $I_D \cong 20\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$ | | 20 | 30 | ns |
| Rise Time | t_r | | | 11 | 17 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 77 | 115 | |
| Fall Time | t_f | | | 10 | 15 | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = 20\text{ V}, R_L = 1.0\text{ }\Omega$ $I_D \cong 20\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$ | | 102 | 155 | |
| Rise Time | t_r | | | 62 | 95 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 180 | 270 | |
| Fall Time | t_f | | | 60 | 90 | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continuous Source-Drain Diode Current | I_S | $T_C = 25\text{ }^{\circ}\text{C}$ | | | 110 | A |
| Pulse Diode Forward Current ^a | I_{SM} | | | | 200 | |
| Body Diode Voltage | V_{SD} | $I_S = 20\text{ A}$ | | 0.8 | 1.2 | V |
| Body Diode Reverse Recovery Time | t_{rr} | $I_F = 20\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^{\circ}\text{C}$ | | 50 | 75 | ns |
| Body Diode Reverse Recovery Charge | Q_{rr} | | | 70 | 105 | nC |
| Reverse Recovery Fall Time | t_a | | | 30 | | ns |
| Reverse Recovery Rise Time | t_b | | | 20 | | |

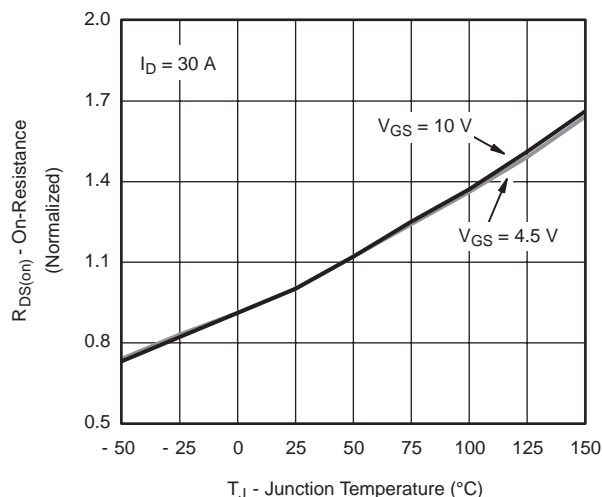
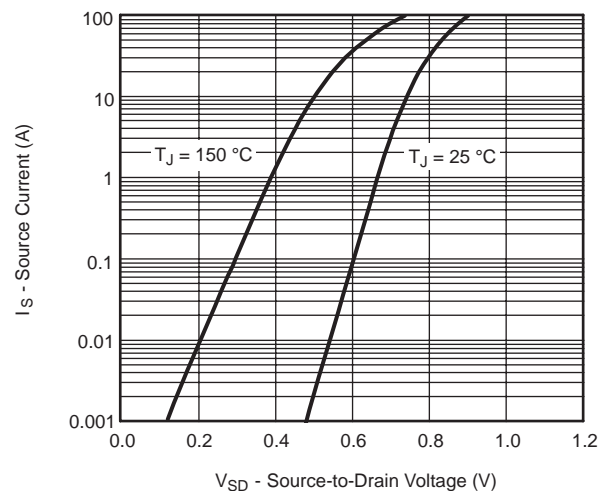
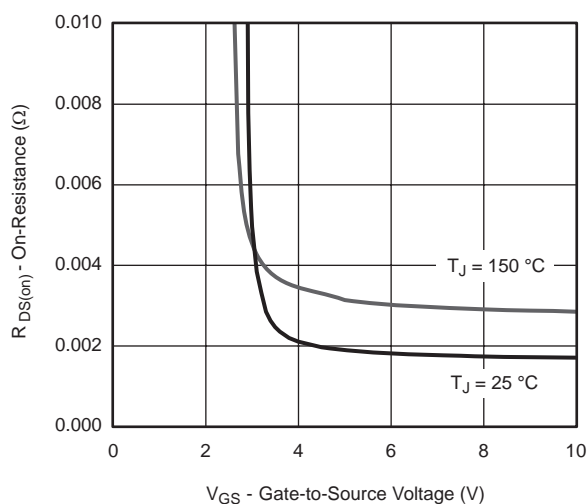
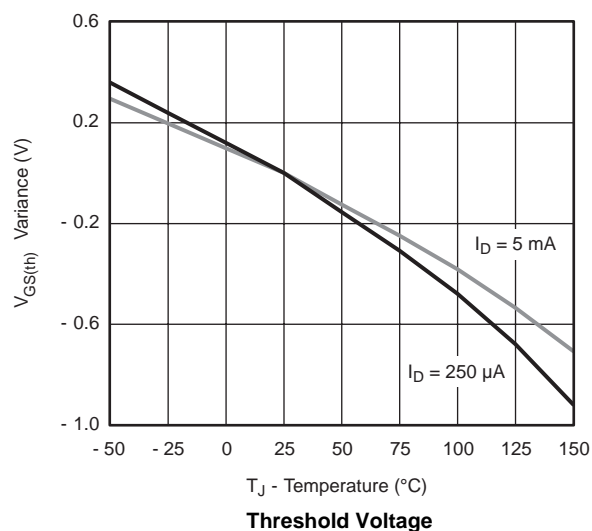
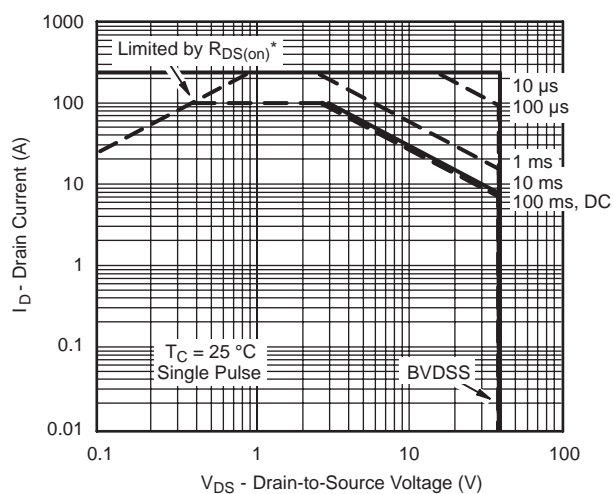
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

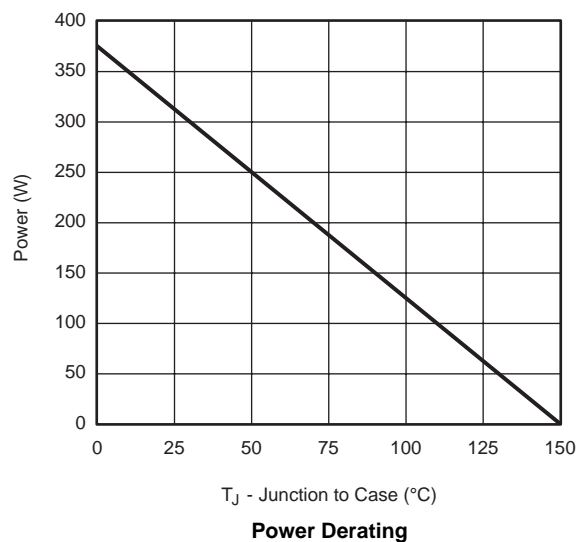
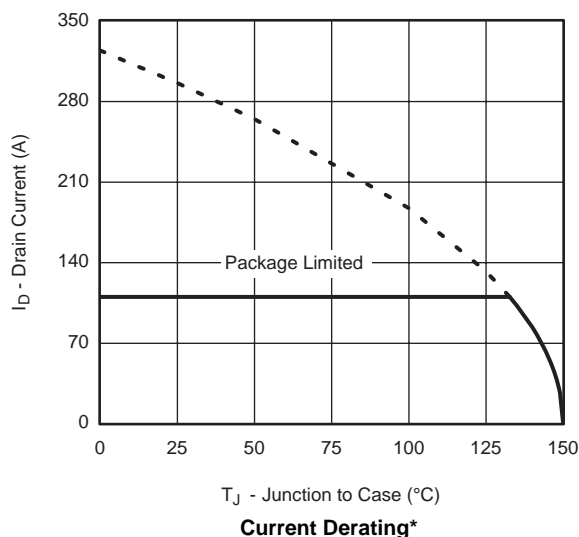
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Output Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance

Gate Charge

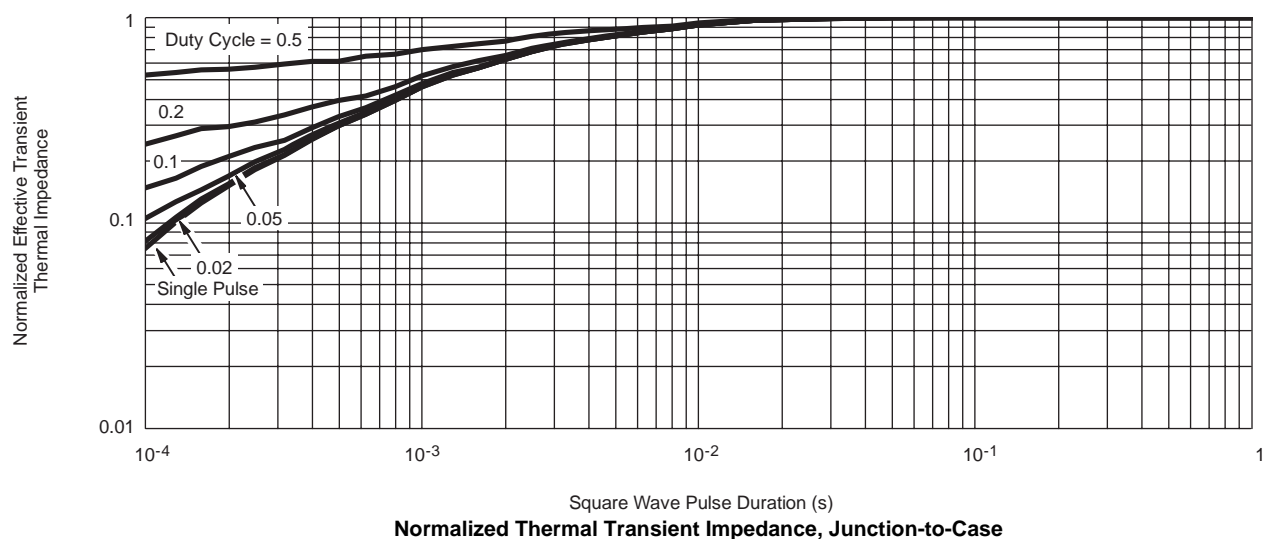
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

On-Resistance vs. Junction Temperature

Forward Diode Voltage vs. Temperature

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

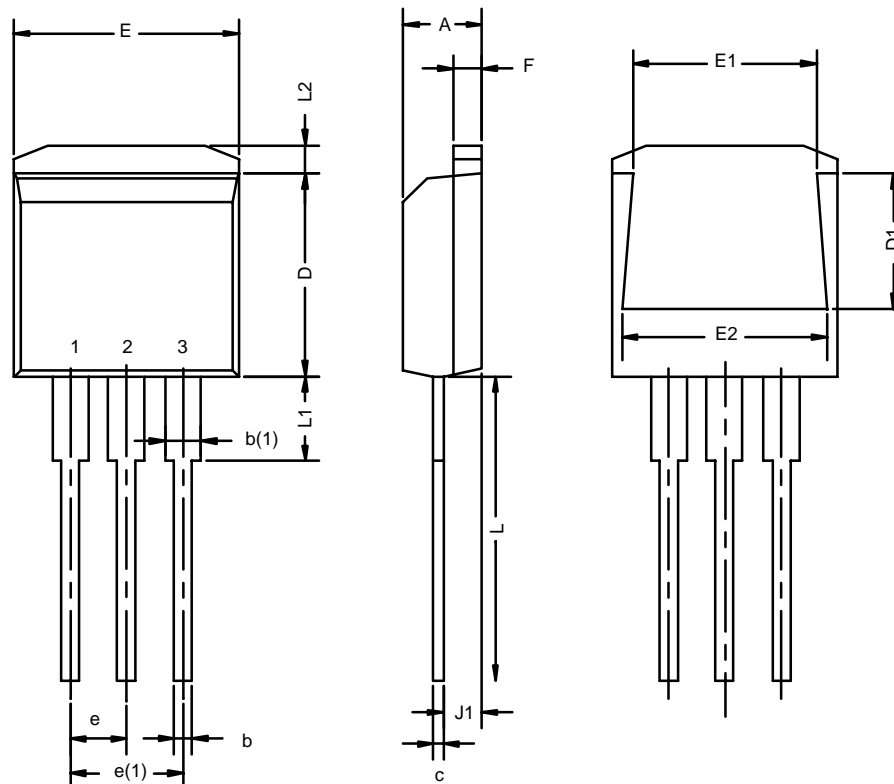
Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


* The power dissipation P_D is based on $T_{J(\max)} = 150^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TO-262: 3-LEAD



| Dim | MILLIMETERS* | | INCHES | |
|---|--------------|-------|--------|-------|
| | Min | Max | Min | Max |
| A | 4.32 | 4.70 | 0.170 | 0.185 |
| b | 0.64 | 1.00 | 0.025 | 0.039 |
| b(1) | 1.14 | 1.40 | 0.045 | 0.055 |
| c | 0.36 | 0.50 | 0.014 | 0.020 |
| D | 8.64 | 9.65 | 0.340 | 0.380 |
| D1 | 5.59 | 6.10 | 0.220 | 0.240 |
| e | 2.41 | 2.67 | 0.095 | 0.105 |
| e(1) | 4.95 | 5.33 | 0.195 | 0.210 |
| E | 10.03 | 10.41 | 0.395 | 0.410 |
| E1 | 7.87 | 8.64 | 0.310 | 0.340 |
| E2 | 9.02 | 9.53 | 0.355 | 0.375 |
| F | 1.14 | 1.40 | 0.045 | 0.055 |
| J1 | 2.41 | 2.79 | 0.095 | 0.110 |
| L | 13.08 | 14.22 | 0.515 | 0.560 |
| L1 | - | 3.81 | - | 0.150 |
| L2 | 1.02 | 1.40 | 0.040 | 0.055 |
| ECN: T-02234—Rev. C, 14-Oct-02 DWG: 5855 | | | | |

*Use millimeters as the primary measurement

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